#### Overall procedure to determine parameter values



- The dynamic data  $\{i[k], v[k]\}$  are used to identify all ESC model parameter values (except OCV vs. SOC relationship)
  - 1. First, compute  $\eta$  and Q from data, directly, as we did for the OCV test results
  - 2. Compute z[k], OCV(z[k]) for every data sample; subtract OCV from v[k]
  - 3. Use subspace system identification technique to find R-C time constants
  - 4. Compute s[k],  $i_R[k]$  for every data sample
  - 5. Guess value for  $\gamma$ ; using  $\gamma$ , compute h[k] for every data sample
  - 6. "Unexplained" part of voltage is now linear in parameters—solve for these parameter values using least squares
  - 7. Compute rms voltage-prediction error of present model
  - 8. Adapt  $\gamma$  to minimize this error, iterating steps 5–8 until convergence is reached

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#### 1a. Compute coulombic efficiency



- First, use data set collected for test temperature 25 °C
- Since  $\eta[k] = \eta(25^{\circ}\text{C})$  in all steps, compute

 $\eta(25\,^{\circ}\text{C}) = \frac{\text{total absolute ampere-hours discharged in all steps at } 25\,^{\circ}\text{C}}{\text{total absolute ampere-hours charged in all steps at } 25\,^{\circ}\text{C}}$ 

 Next, for data sets collected where test temperature was not 25 °C, compute coulombic efficiency at test temperature T

$$\eta(T) = \frac{\text{total absolute ampere-hours discharged}}{\text{total absolute ampere-hours charged at temperature }T} \\ - \eta(25\,^{\circ}\text{C}) \frac{\text{total absolute ampere-hours charged at 25\,^{\circ}\text{C}}}{\text{total absolute ampere-hours charged at temperature }T}$$

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# 1b. Compute total capacity



- First, use data set collected for test temperature 25 °C
- Sum over all data in steps 1–5, gives *Q* in ampere-seconds

$$Q(25\,^{\circ}\text{C}) = \sum_{j=0}^{k-1} \eta[j]i[j]$$

■ For data sets collected for test temperatures different from 25 °C, sum over all data in steps 1–5, again gives Q in ampere-seconds

$$1 = \sum_{\text{data at } 25 \,^{\circ}\text{C}} \frac{\eta(25 \,^{\circ}\text{C})i[j]}{Q(25 \,^{\circ}\text{C})} + \sum_{\text{data at } T} \frac{\eta(T)i[j]}{Q(T)}$$

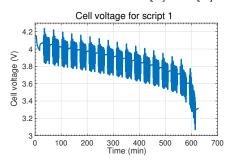
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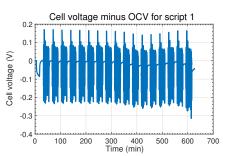
# 2. Subtract OCV from voltage



- Now, compute SOC for every point  $z[k] = 1 \sum_{j=0}^{k-1} \frac{\eta[k]i[k]}{Q}$
- Then, compute modified (as-yet unexplained) voltage

$$\tilde{v}[k] = v[k] - \mathsf{OCV}(z[k], T[k])$$





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### 3. Finding R–C time constants



- Now desire to find diffusion-voltages R—C time constants
- Could use nonlinear optimization to guess and adapt values (together with other unknown parameter values), to minimize rms voltage error
- Nonlinear optimization is slow, not guaranteed to find optimal solution
- Subspace system identification replaces nonlinear optimization with linear-algebra technique that finds solution in one step
- Unfortunately, while computationally simple, its derivation is too complex to teach in this specialization—provided sample code implements the solution, however
- For more info, cf. http://mocha-java.uccs.edu/ECE5560

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# 4–5. Compute $i_R[k], s[k], h[k]$



- We don't know hysteresis rate constant  $\gamma$ , so we start by guessing a value, which we will later refine
- Can then compute all model states (cf. slide 12 for definitions of  $A_{RC}$ ,  $B_{RC}$ ,  $A_H$ )

$$\begin{split} i_R[k] &= A_{RC} i_R[k-1] + B_{RC} i[k-1] \\ s[k] &= \begin{cases} \operatorname{sgn}(i[k]), & |i[k]| > 0; \\ s[k-1], & \text{otherwise} \end{cases} \\ h[k] &= A_H[k-1]h[k-1] + (A_H[k-1]-1)\operatorname{sgn}(i[k-1]) \end{split}$$

■ Generally initialize  $i_R[0] = 0$ ; h[0] = 1; s[0] = -1



### 6. Solve for linear output parameters

Unexplained part of the measured cell voltage is

$$\tilde{v}[k] = v[k] - \text{OCV}(z[k], T[k])$$
  
=  $Mh[k] + M_0s[k] - \sum_j R_j i_{R_j}[k] - R_0i[k]$ 

We can solve this for the unknowns

$$\underbrace{\begin{bmatrix} \tilde{v}[1] \\ \tilde{v}[2] \\ \vdots \end{bmatrix}}_{Y} = \underbrace{\begin{bmatrix} h[1] & s[1] & -i[1] & -i^{T}_{R_{j}}[1] \\ h[2] & s[2] & -i[2] & -i^{T}_{R_{j}}[2] \\ \vdots & \vdots & \vdots & \vdots \end{bmatrix}}_{A} \underbrace{\begin{bmatrix} M \\ M_{0} \\ R_{0} \\ R_{j} \end{bmatrix}}_{Y},$$

via least-squares solution X = A\Y in Octave/MATLAB

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### 7. Compute rms voltage prediction error



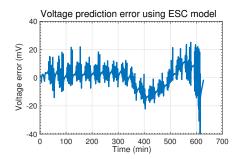
- Desire model prediction to approximate true voltage closely
- For present set of parameter values, model predicts voltage

$$\hat{v}[k] = \text{OCV}(z[k]) + Mh[k] + M_0s[k] - \sum_i R_i i_{R_i}[k] - R_0i[k]$$

Can use rms error as an indicator of model fit

rms = 
$$\sqrt{\frac{1}{N} \sum_{j=1}^{N} (v[k] - \hat{v}[k])^2}$$

Desire that rms be as small as possible (graph shown has rms error of 5.7 mV)



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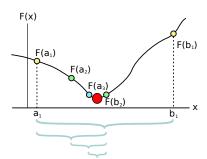
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2.3.2: How are cell data used to find dynamic model parameter values?

# 8. Iterate to find best $\gamma$



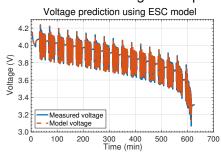
- Now, iterate to find "best" value for  $\gamma$
- Bisection search is one simple possibility
  - $\square$  Select bounded range for  $\gamma$ , between  $a_1$  and  $b_1$
  - Evaluate rms error for models computed with  $\gamma = a_1$  and  $\gamma = b_1$
  - $\Box$  Evaluate rms error for model computed with  $\gamma$ equal to the midpoint of  $a_1$  and  $b_1$
  - $\Box$  Replace endpoint  $a_1$  or  $b_1$  having worst rms error with midpoint
  - $\Box$  Iterate until satisfied "close enough" to best  $\gamma$

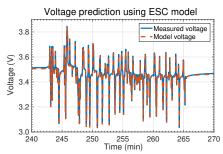


#### Final result



- Final model is able to predict cell voltage very well
- Figures show model having 3 R—C pairs; rms error of 5.7 mV





Improvement can be made with additional R-C pairs; however, error graph on slide 8 suggests that OCV refinement might provide greater benefit

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2.3.2: How are cell data used to find dynamic model parameter values?

#### Summary



- Have now seen how to process dynamic data to find all parameter values for ESC model
  - 1. Compute  $\eta$  and Q
  - Compute z[k], OCV(z[k]); subtract OCV from v[k]
  - Use subspace system identification technique to find R–C time constants
  - 4–5. Guess value for  $\gamma$ ; compute s[k],  $i_R[k]$ , h[k]
  - Solve for remaining parameter values using least squares
  - 7–8. Compute rms voltage-prediction error, adapt  $\gamma$  to minimize this error, iterating steps 5-8 until convergence is reached
- Final model predicts true cell voltage with high fidelity

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2.3.2: How are cell data used to find dynamic model parameter values?

#### Credits



Credits for photos in this lesson

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In the earlier slides, note that

$$A_{RC} = \begin{bmatrix} \exp\left(\frac{-\Delta t}{R_1 C_1}\right) & 0 & \cdots \\ 0 & \exp\left(\frac{-\Delta t}{R_2 C_2}\right) \\ \vdots & \ddots \end{bmatrix}, \qquad B_{RC} = \begin{bmatrix} \left(1 - \exp\left(\frac{-\Delta t}{R_1 C_1}\right)\right) \\ \left(1 - \exp\left(\frac{-\Delta t}{R_2 C_2}\right)\right) \\ \vdots & \vdots \end{bmatrix}$$
$$A_H[k] = \exp\left(-\left|\frac{\eta[k]i[k]\gamma \Delta t}{Q}\right|\right)$$